Ordering number : EN2101E

2SA1507/2SC3902

ON Semiconductor®

http://onsemi.com

Bipolar Transistor

(-)160V, (-)1.5A, Low VCE(sat), (PNP)NPN Single TO-126ML

Applications

· Color TV audio output, converters, inverters

Features

- · Adoption of FBET and MBIT process High breakdown voltage Large current capacity
- The plastic-covered heat sink eliminates the need for an insulator when mounting the 2SA1507/2SC3902

Specifications (): 2SA1507

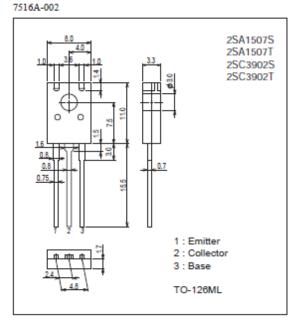
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)180	٧
Collector-to-Emitter Voltage	VCEO		(-)160	٧
Emitter-to-Base Voltage	VEBO		(-)6	٧
Collector Current	IC		(-)1.5	Α
Collector Current (Pulse)	ICP		(-)2.5	Α
Collector Dissipation	PC		1.5	W
		Tc=25*C	10	W
Junction Temperature	Tj		150	*C
Storage Temperature	Tstg		-55 to +150	•C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

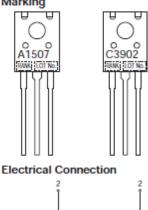
unit: mm (typ)



Product & Package Information

: TO-126ML Package JEITA, JEDEC : TO-126 Minimum Packing Quantity : 200 pcs./bag

Marking



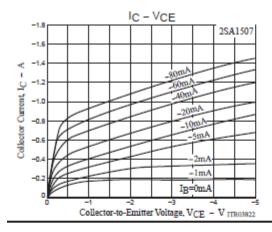


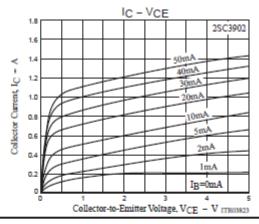
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			11.5
Parameter		Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	VCB=(-)120V, IE=0A			(-)1.0	μΑ
Emitter Cutoff Current	IEBO	VEB=(-)4V, IC=0A			(-)1.0	μΑ
DC Current Gain	hpg1	V _{CE} =(-)5V, I _C =(-)100mA	100°		400°	
	hpE2	V _{CE} =(-)5V, I _C =(-)10mA	90			
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)50mA		120		MHz
Output Capacitance	Cob	VCB=(-)10V, f=1MHz		(22)14		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=(-)500mA, IB=(-)50mA		(-0.2)0.13	(-0.5)0.45	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =(-)500mA, I _B =(-)50mA		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =(-)10μΑ, I _E =0Α	(-)190			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =(-)1mA, R _{BE} =∞	(-)160			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=(-)10μA, IC=0A	(-)6			V
Turn-On Time	ton			(0.7)0.04		μs
Storage Time	t _{stq}	See specified Test Circuit.		(0.7)1.2		μs
Fall Time	tf			(0.04)0.08		μs

*: The 2SA1507 / 2SC3902 are classified by 100mA hpg as follows:

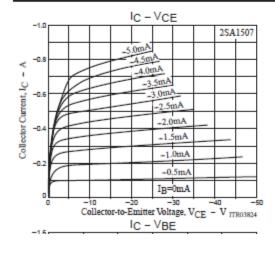
	Rank	R	S	T	
1	hFE	100 to 200	140 to 280	200 to 400	

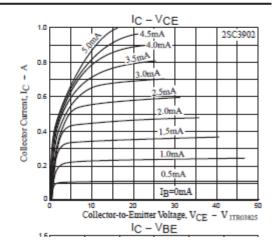


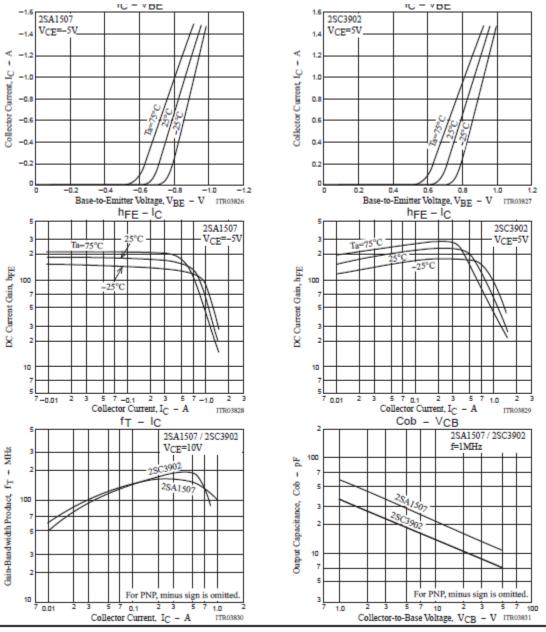


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2SA1507 / 2SC3902







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